

Belle II Pixel Detector

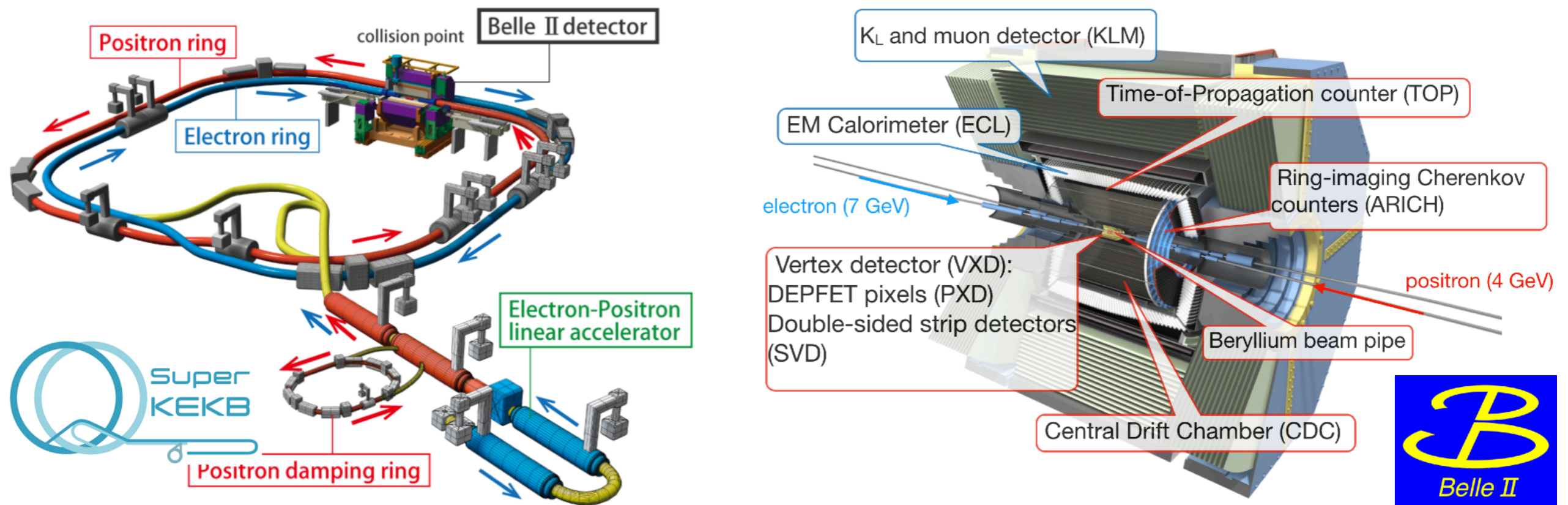
Commissioning and Performance

Hua Ye

On behalf of Belle II PXD - DEPFET Collaboration

HSTD12, Dec.14-18, 2019, Hiroshima

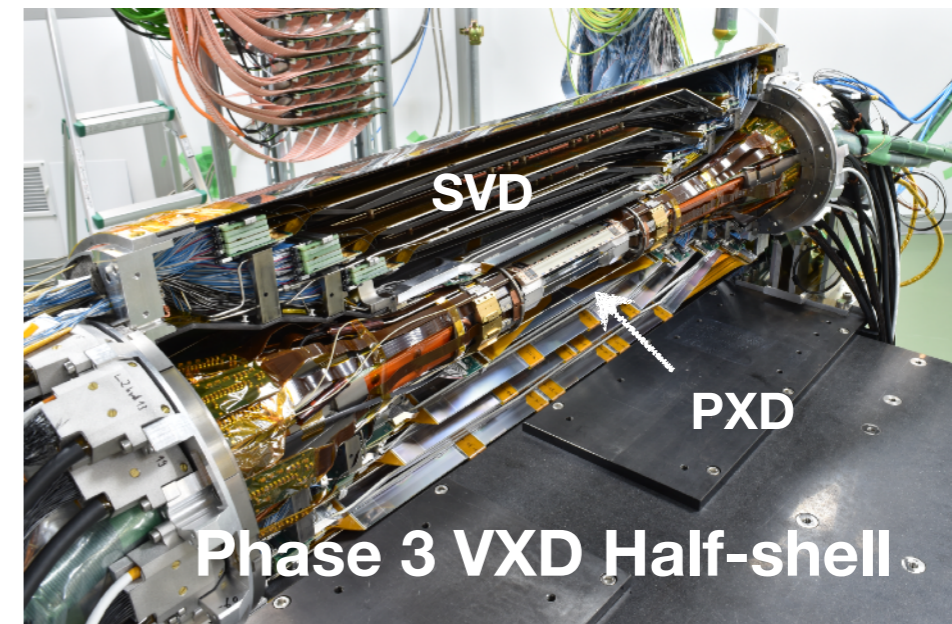
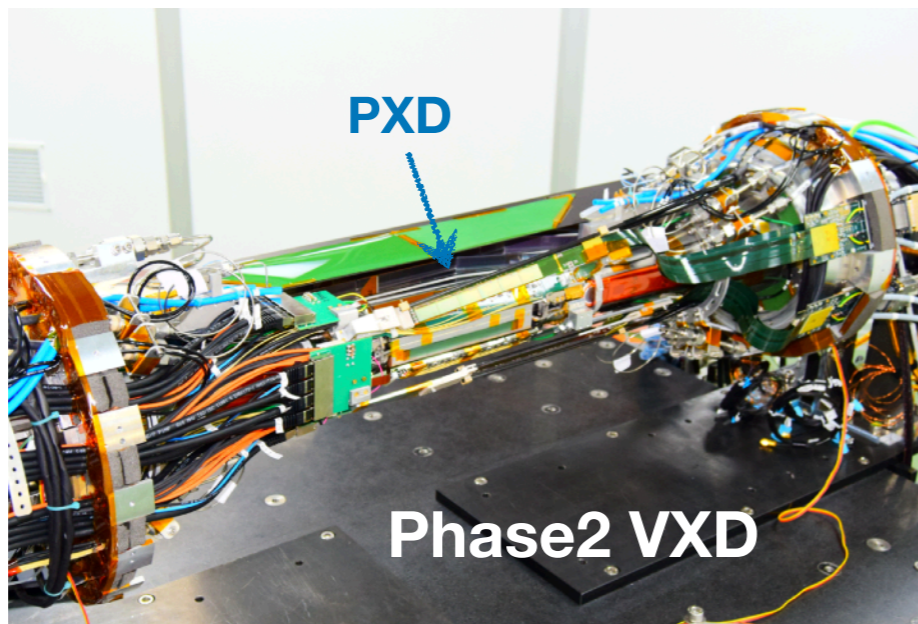
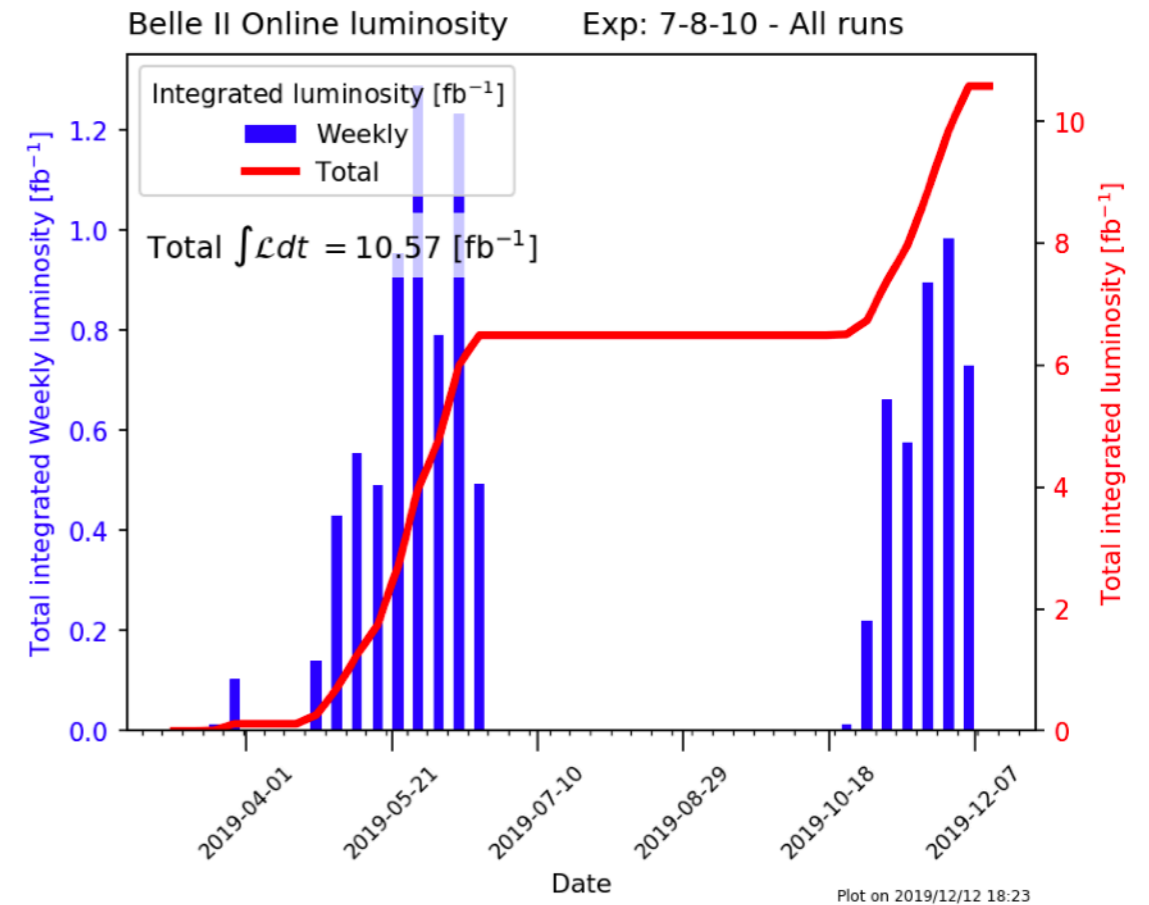
SuperKEKB and Belle II



- ❖ SuperKEKB delivers e^+e^- collisions at 10.58 GeV ($M_{\Upsilon(4S)}$), with a target peak luminosity of $8 \times 10^{35} \text{ cm}^{-2}\text{s}^{-1}$, 40 times larger than that of KEKB.
 - ❖ Increase beam currents twice
 - ❖ Reduce vertical beam spot size by a factor of 20
- ❖ Belle II detector has accomplished a series of upgrades to
 - ❖ Improve the overall performance
 - ❖ Cope with the increased background and high trigger rate.
- ❖ Aim to accumulate a dataset of 50 ab^{-1} by ~ 2027 , to study flavour physics and explore new physics beyond the standard model.

Highlights of Belle II Status

- ❖ Collisions started in Spring 2018, “Phase 2”.
 - ❖ Mainly for beam commissioning,
 - ❖ with a dedicated vertex detector to study beam background.
 - ❖ **0.5 fb⁻¹ data recorded.**
- ❖ Physics data taking has started in March 2019, “Phase 3”.
 - ❖ With Belle II VXD
 - ❖ **10 fb⁻¹ data recorded.**
 - ❖ Aim to collect 200 fb⁻¹ by summer 2020.
- ❖ On Dec.3, Belle II achieved to record data at luminosities in excess of 10³⁴ cm⁻²s⁻¹ (KEKB design luminosity)



DEPFET PXD for Belle II

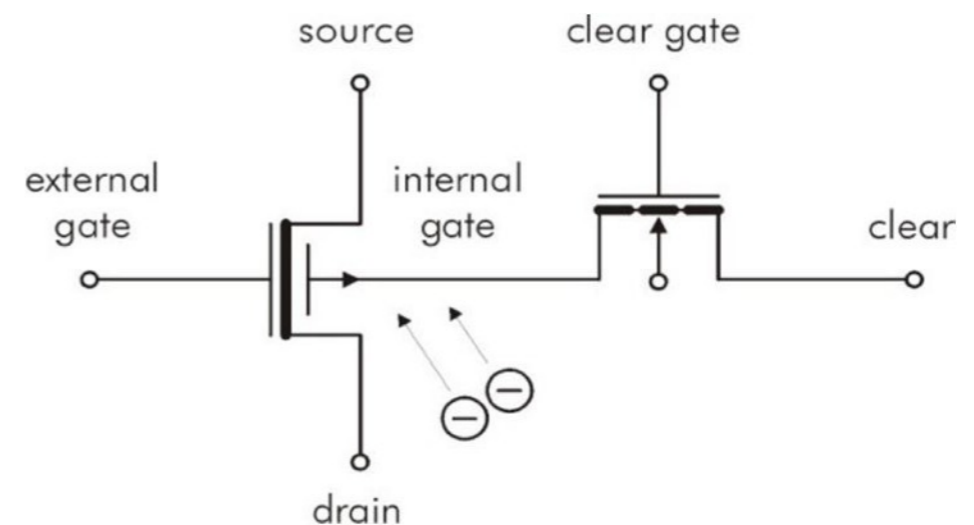
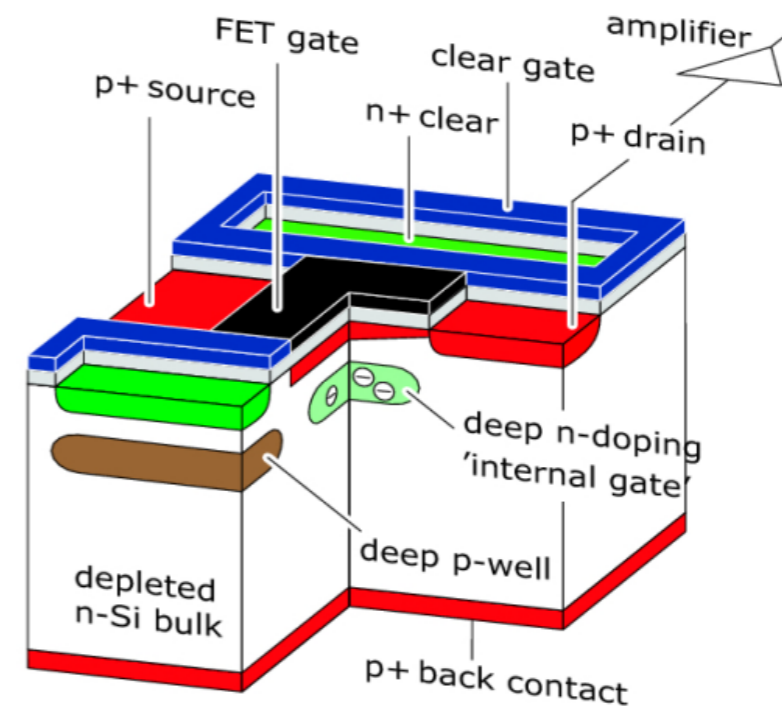
Depleted P-channel Field-Effect Transistor (DEPFET) combines detection and amplification within one device.

Each pixel is a p-channel FET on top of fully depleted silicon bulk

- ❖ Fast charge collection (~ns)
- ❖ Charges collected in the “internal gate”
- ❖ Readout of modulated drain current
 - ➔ internal amplification

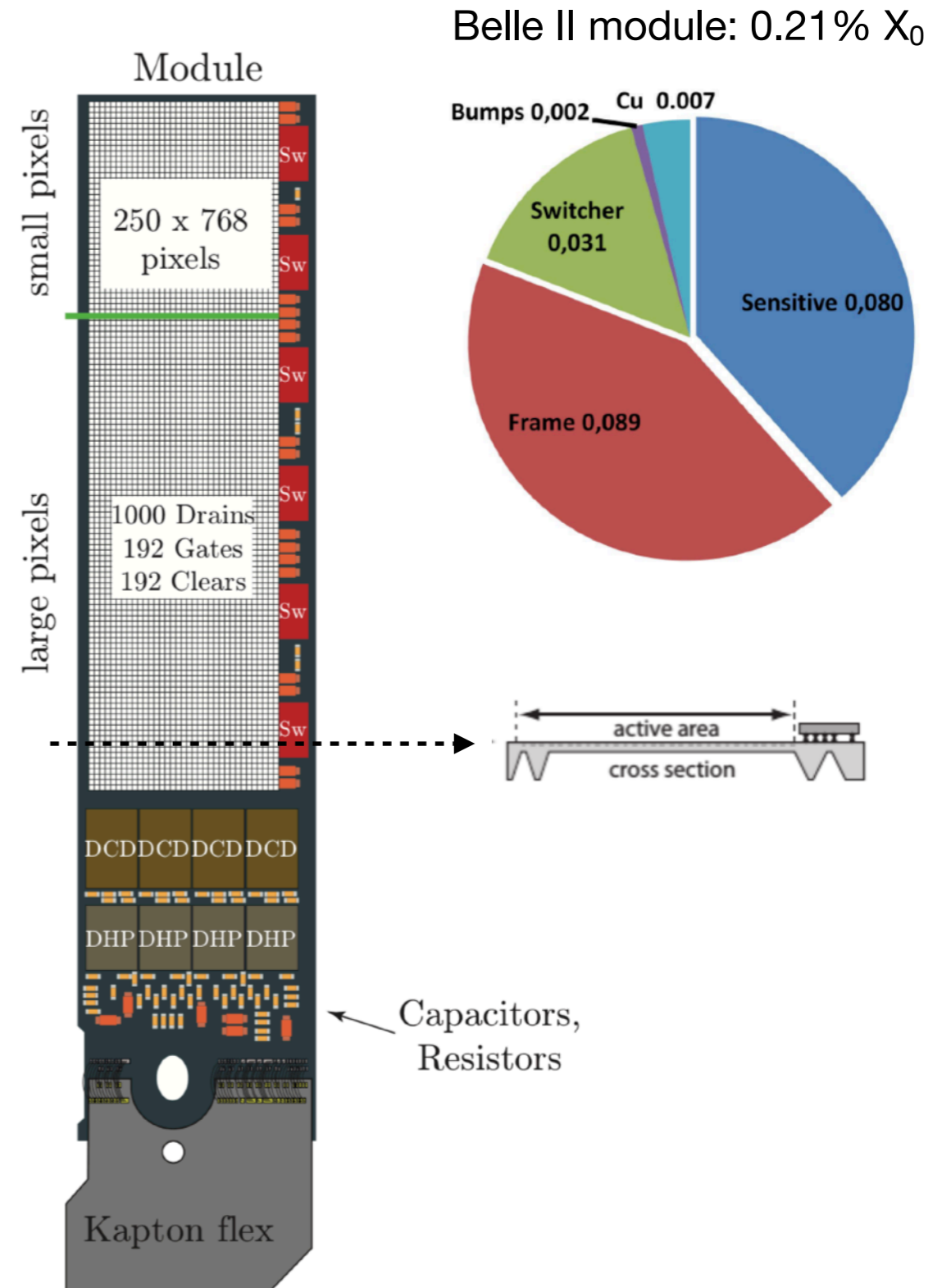
$$g_q = \frac{\partial I}{\partial q} \approx 500 \frac{\text{pA}}{e^-}$$

- ❖ High Signal to Noise Ratio (SNR)
- ❖ Periodical clearing of “internal gate” required to reset the pixel



PXD Module Concept

- ❖ Pixel size: varies in z direction, $50 \times 55\text{-}85 \mu\text{m}^2$
 - ❖ optimized to have the best resolution in forward direction around 45° incident angle
- ❖ 250 x 768 pixels per module
- ❖ By thinning the active sensor thickness can be reduced to as little as $50 \mu\text{m}$.
- ❖ For optimal position resolution (COG) $75\mu\text{m}$ were chosen for PXD
- ❖ 3 Metal layers for circuitry
 - ❖ 2Al + 1Cu
- ❖ Mechanically self-supporting device



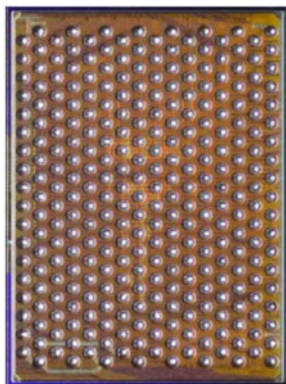
ASICs

DCD: Drain Current Digitizer,

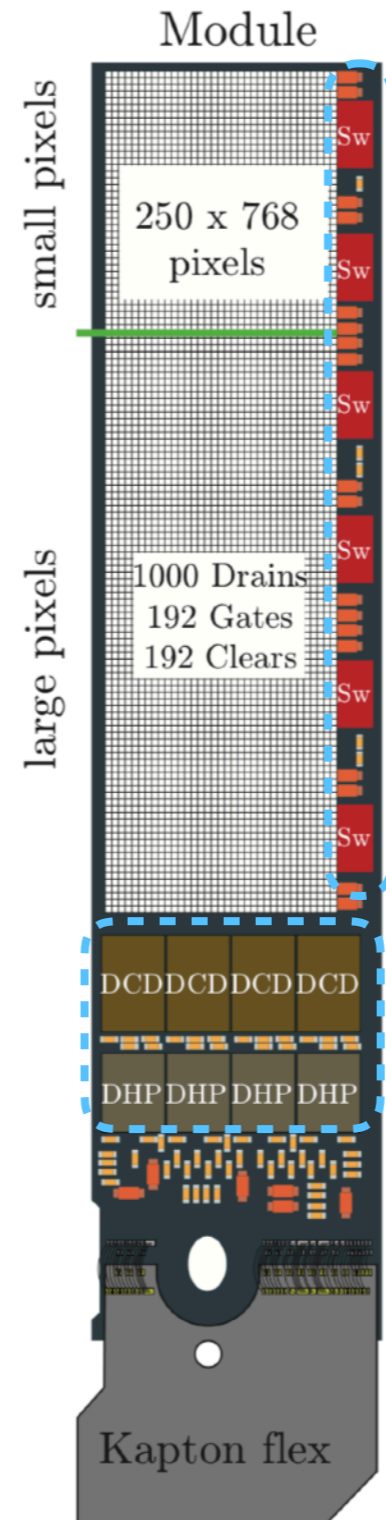


- ❖ UMC 180 nm
- ❖ 256 input channels
- ❖ pipeline 8-bit ADC per channel
- ❖ 92 ns sampling time
- ❖ Rad. hard proved (10 Mrad)

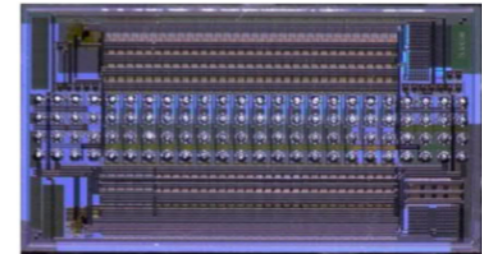
DHP: Data Handling Processor



- ❖ TSMC 65 nm
- ❖ Size 4.0x 3.2 mm²
- ❖ Common mode and pedestal correction
- ❖ Data reduction (zero suppression)
- ❖ Timing and trigger control
- ❖ Transmit 1.6 Gbit/s of data over a 15 m cable to the backend.
- ❖ Rad. Hard proved (100 Mrad)



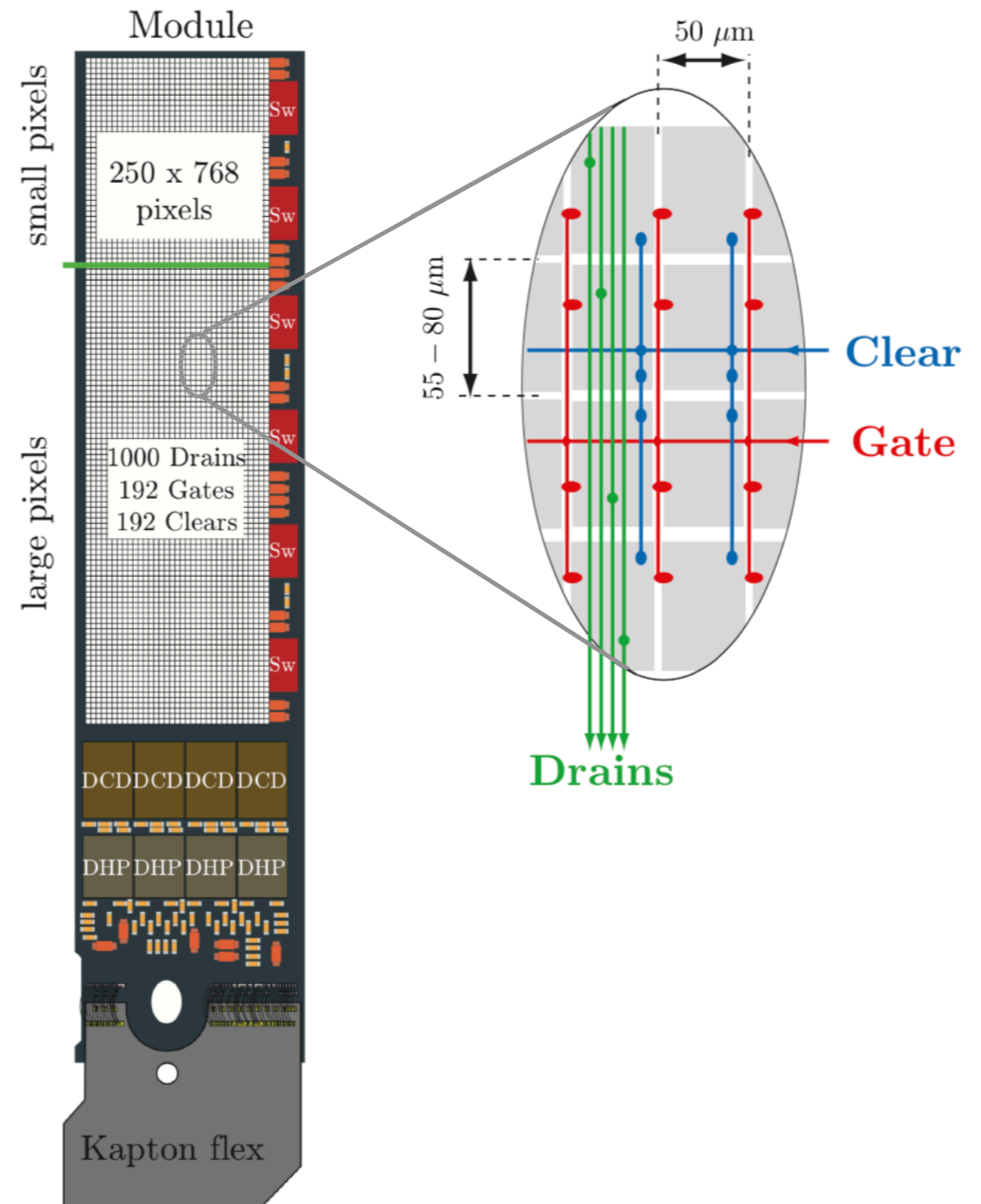
Switcher: Row control



- ❖ AMS/IBM HVCMOS 180 nm
- ❖ Size 3.6 x 1.5 mm²
- ❖ Gate and Clear signal
- ❖ Fast HV ramp for Clear
- ❖ Rad. hard proved (36 Mrad)

Readout Mode

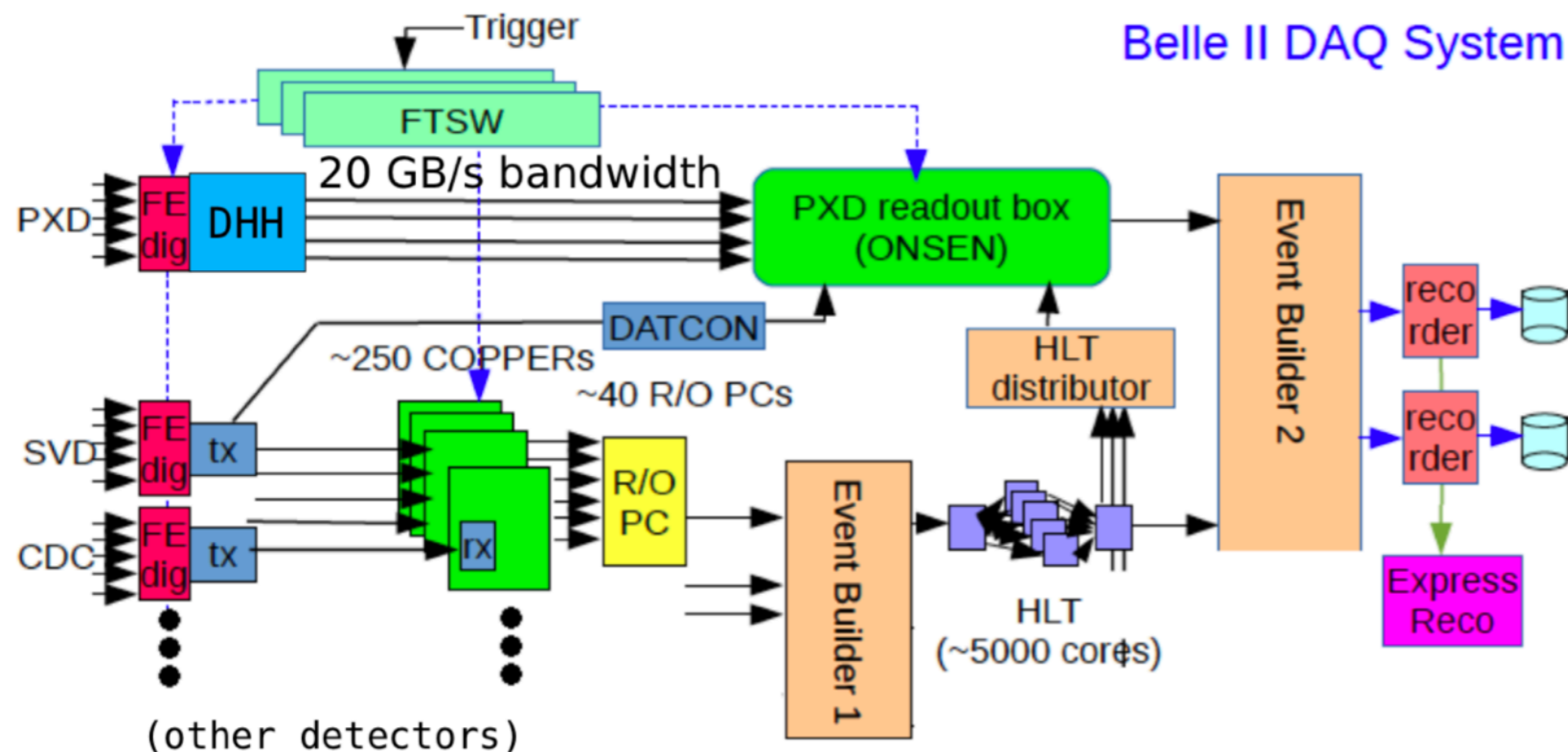
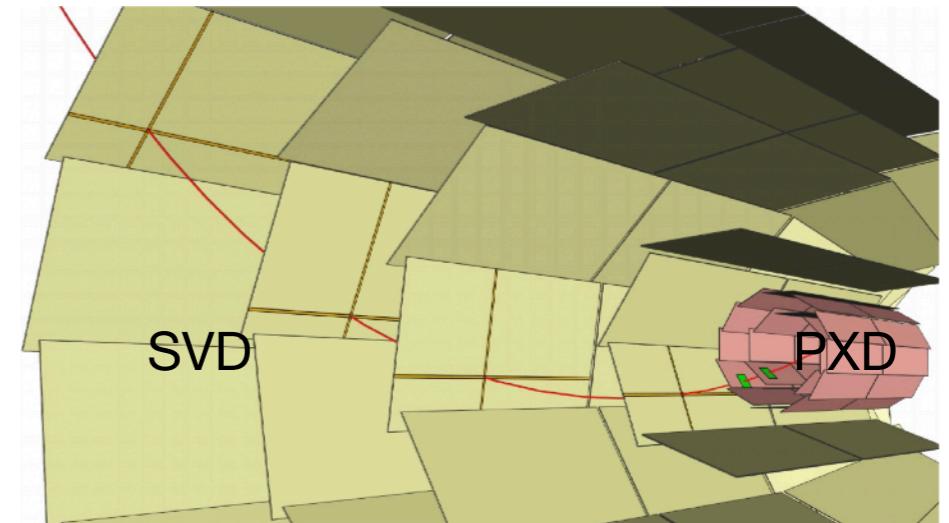
- ❖ Rolling shutter mode
 - ❖ Read signals gate by gate
 - ❖ one gate combines 4 adjacent rows
 - ❖ Read-Clear cycle in $\sim 100\text{ns}$
 - ❖ Full integration time is $20\mu\text{s}$ (twice the revolution time of SuperKEKB)
 - ❖ Only 'activated' rows consume power
 - ❖ Low sensor power consumption
- ❖ Max. acceptable average occupancy $< 3\%$. otherwise,
 - ❖ data loss,
 - ❖ degrade tracking performance.



PXD DAQ Scheme

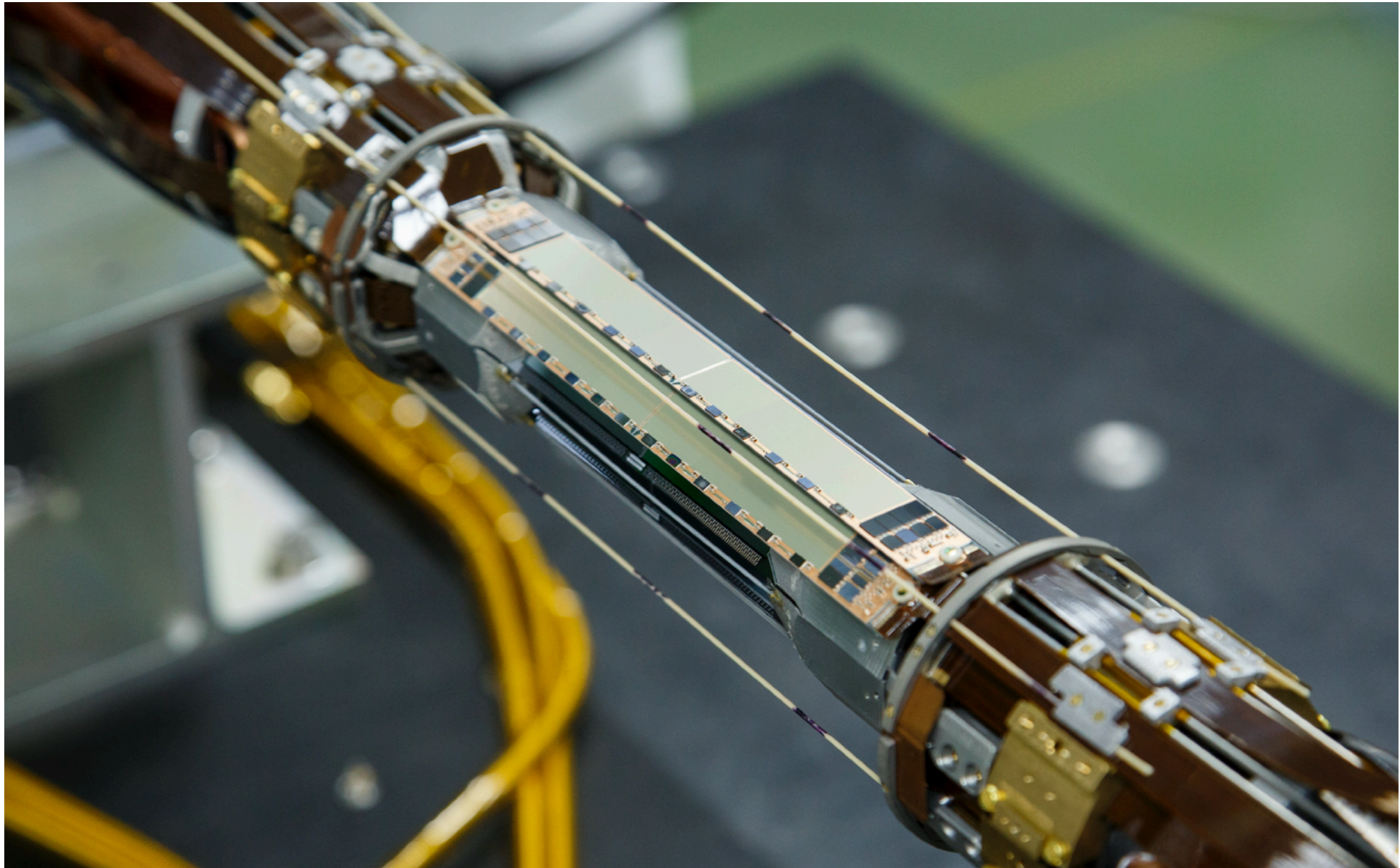
- ❖ PXD unfiltered data rate → 10x sum of other Belle II detectors
 - ❖ Therefore need separate readout path
 - ❖ Data reduction to 1/10 by HLT based ROI calculation from CDC and SVD track information
 - ❖ Feedback to PXD readout, selection of pixels within rectangular ROIs

ROI extrapolation on HLT



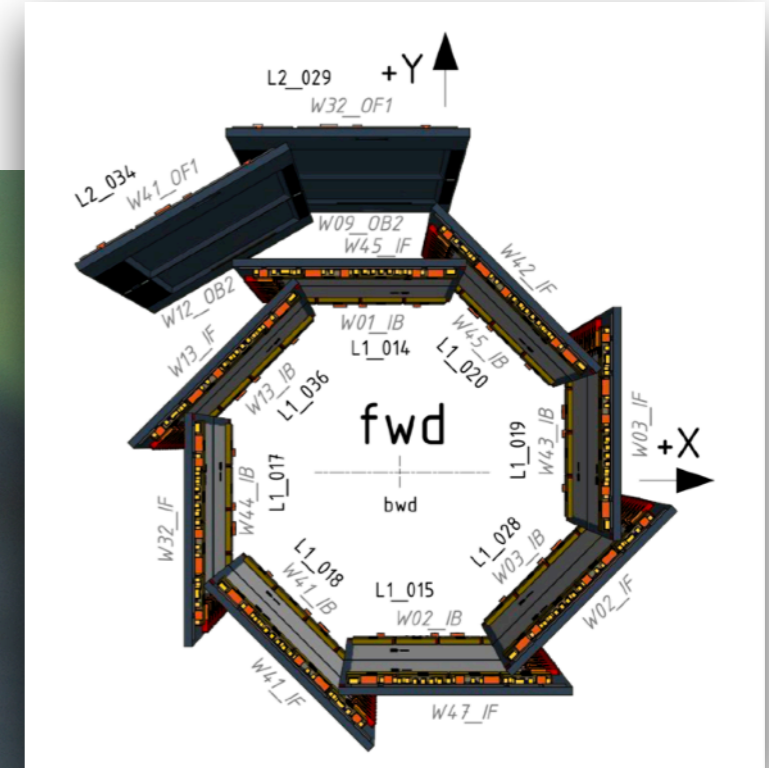
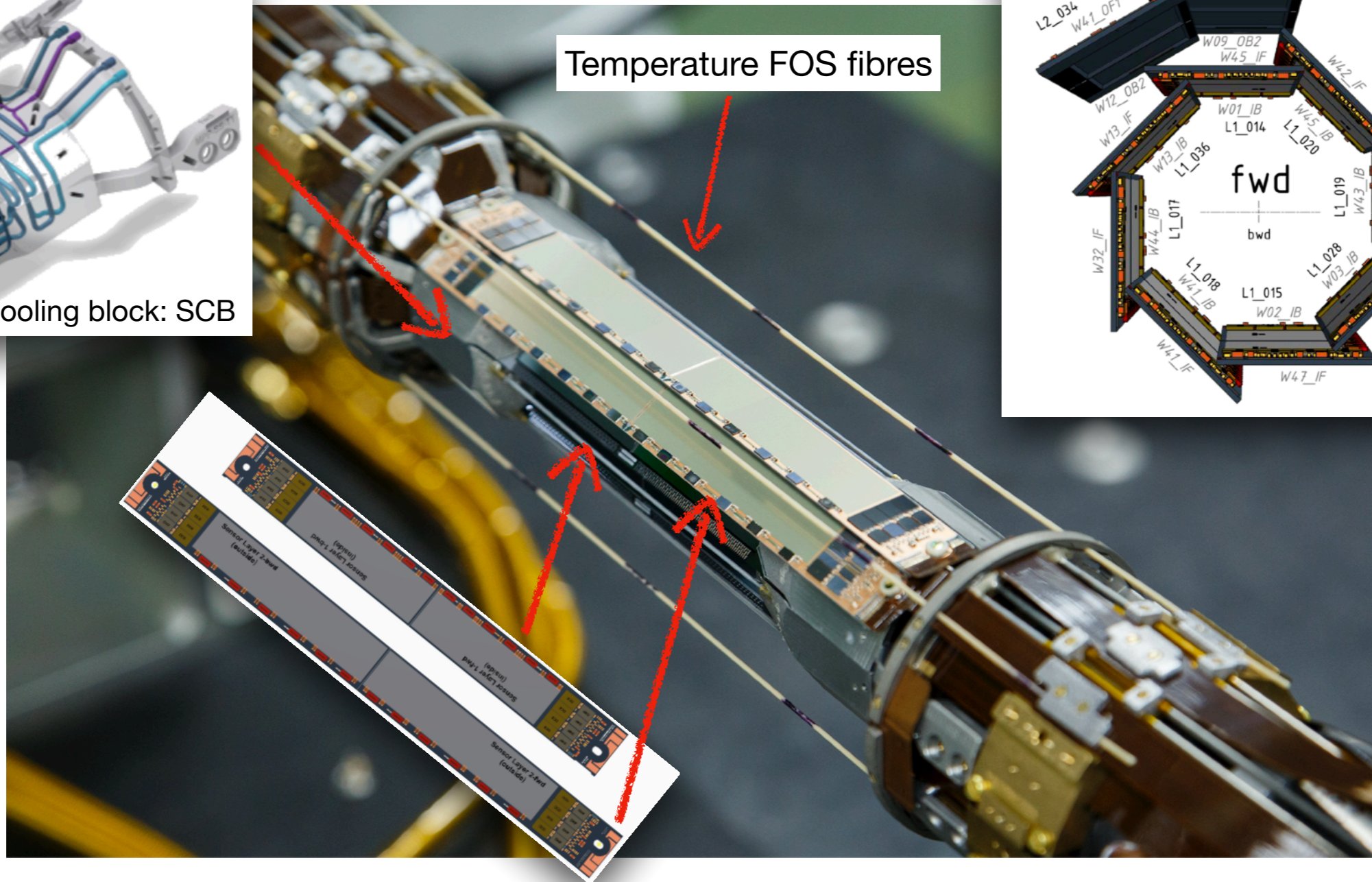
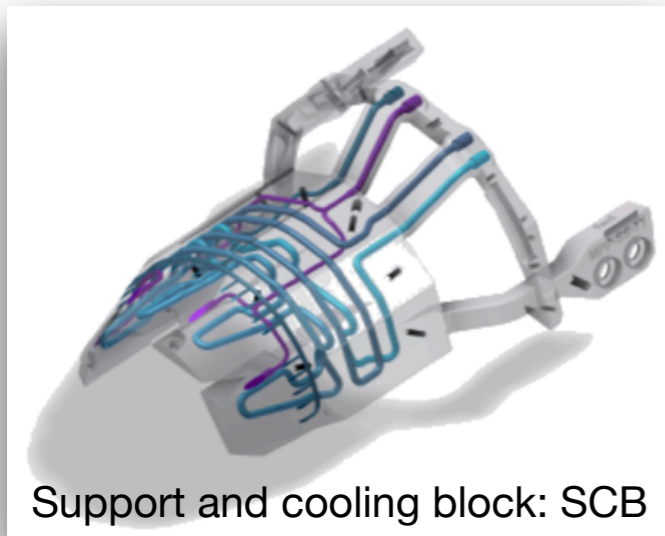
DHH: Data Handling Hub
 HLT: High Level Trigger
 FTSW: Frontend-Timing-Switch
 ROI: Region Of Interest

Belle II PXD for early Phase 3



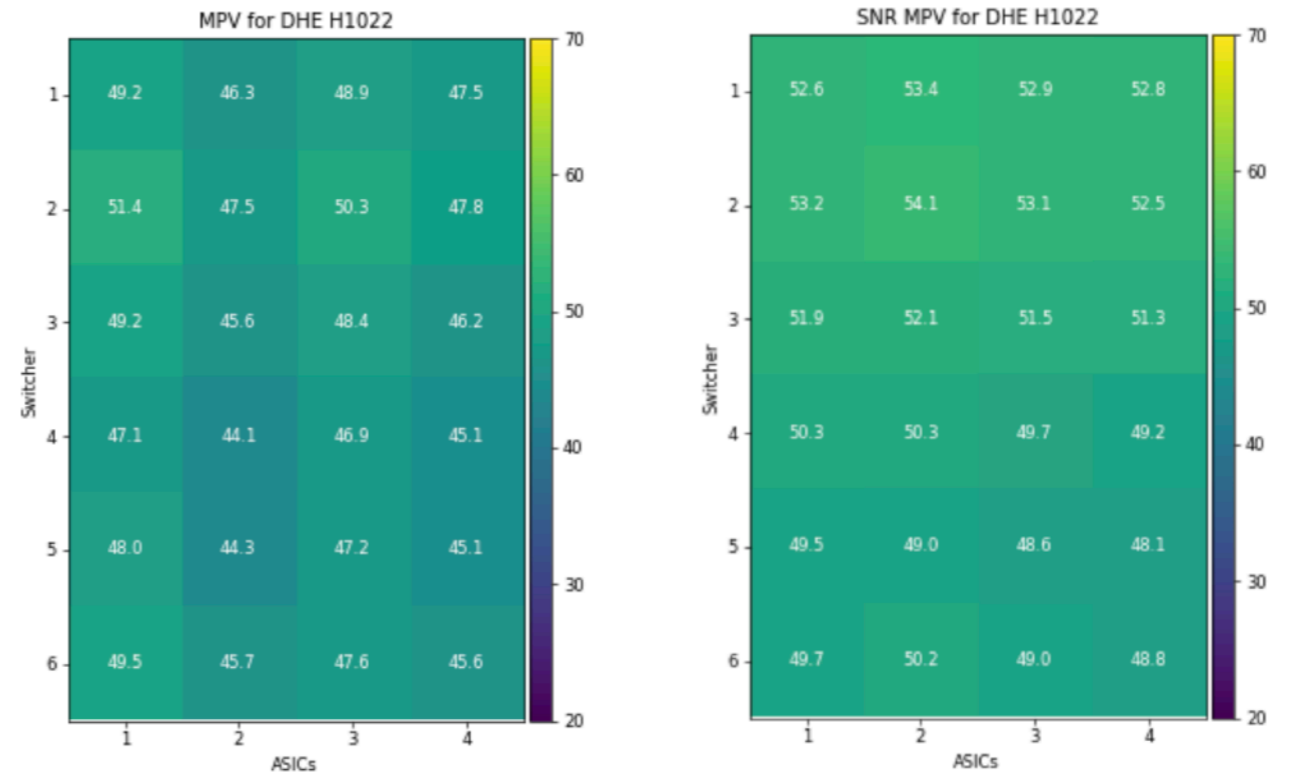
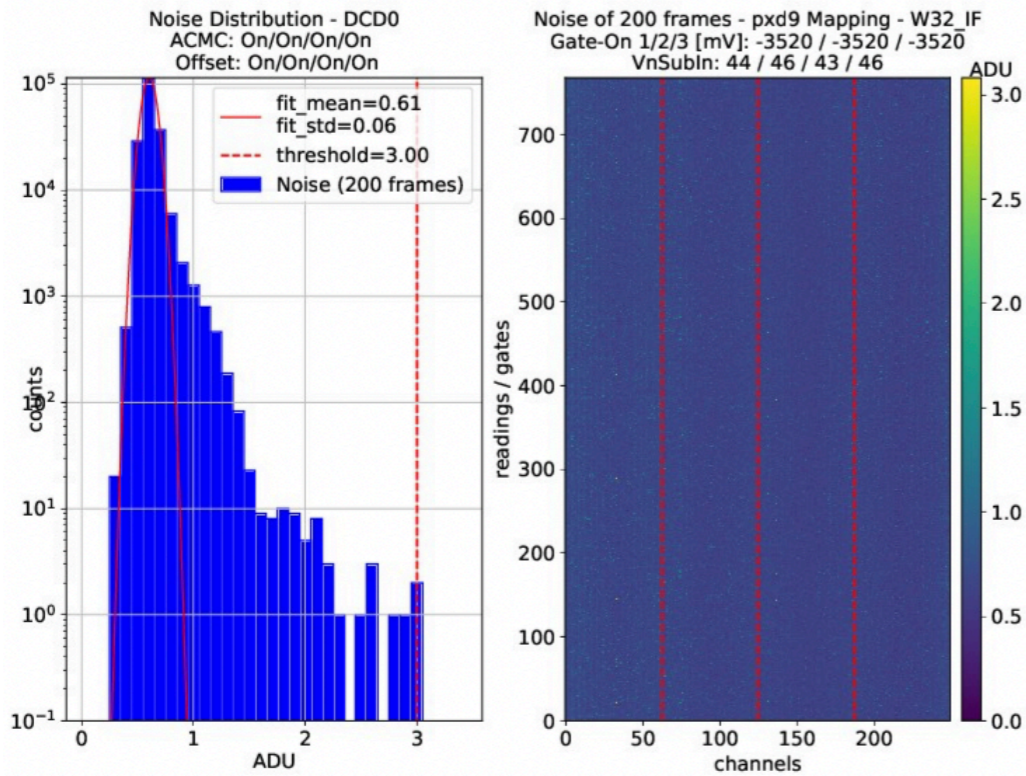
- ❖ 2 layers of DEPFET sensors @ $r = 14(22)$ mm
- ❖ Sensitive area per module: L1: 12.5mm x 44.8mm, L2: 12.5mm x 61.44mm
- ❖ Sensor thickness: 75 μm , 0.21% X_0 per layer

Belle II PXD for early Phase 3

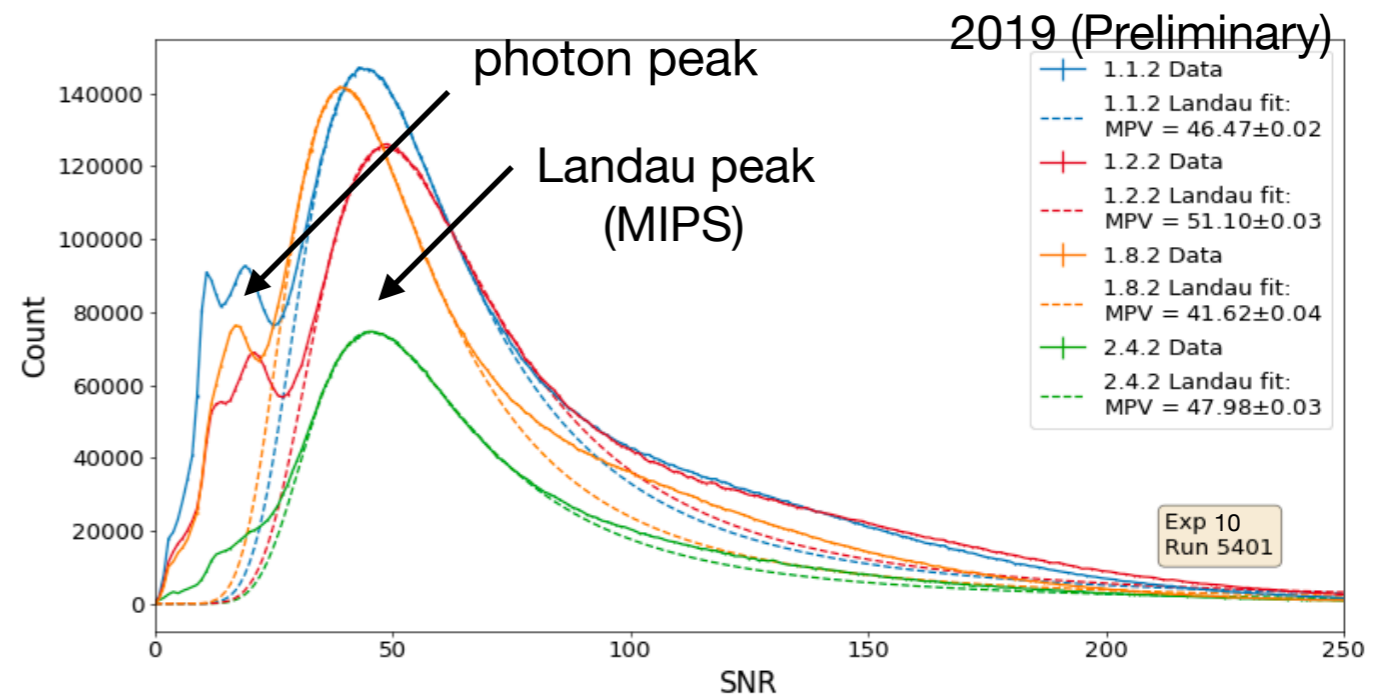


- ❖ Each ladder is formed by a pair of mirrored DEPFET sensors
- ❖ Due to problems in ladder gluing, only half of designed PXD (full L1+2 L2 ladders) was installed in 2018/2019, will be finalized in 2021.

Signal to Noise Ratio

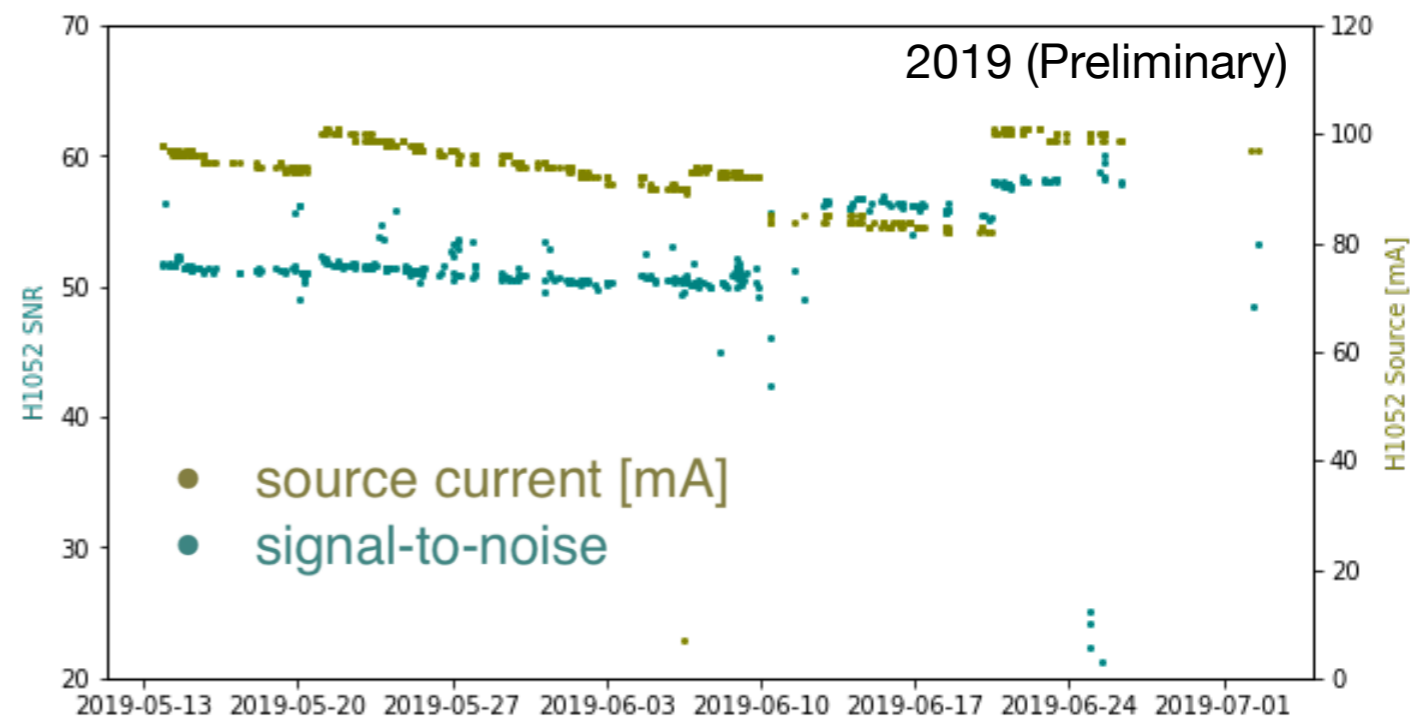
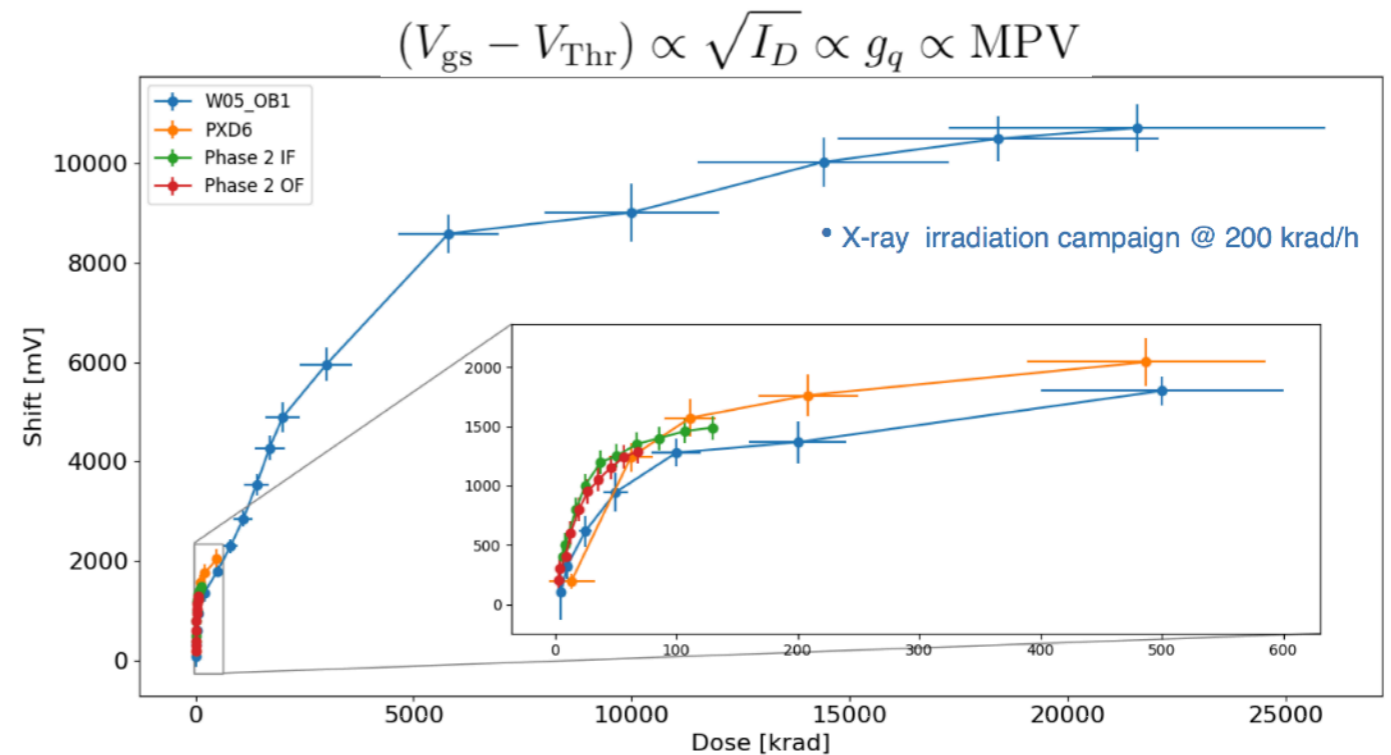


- ❖ Low noise (<1ADU, <100e ENC)
- ❖ Signal to Noise Ratio ≈ 50
- ❖ Most probable value and SNR uniform over ASIC combinations within one module.
- ❖ The inner modules feature more prominent contribution originated from low energy synchrotron radiation photons.

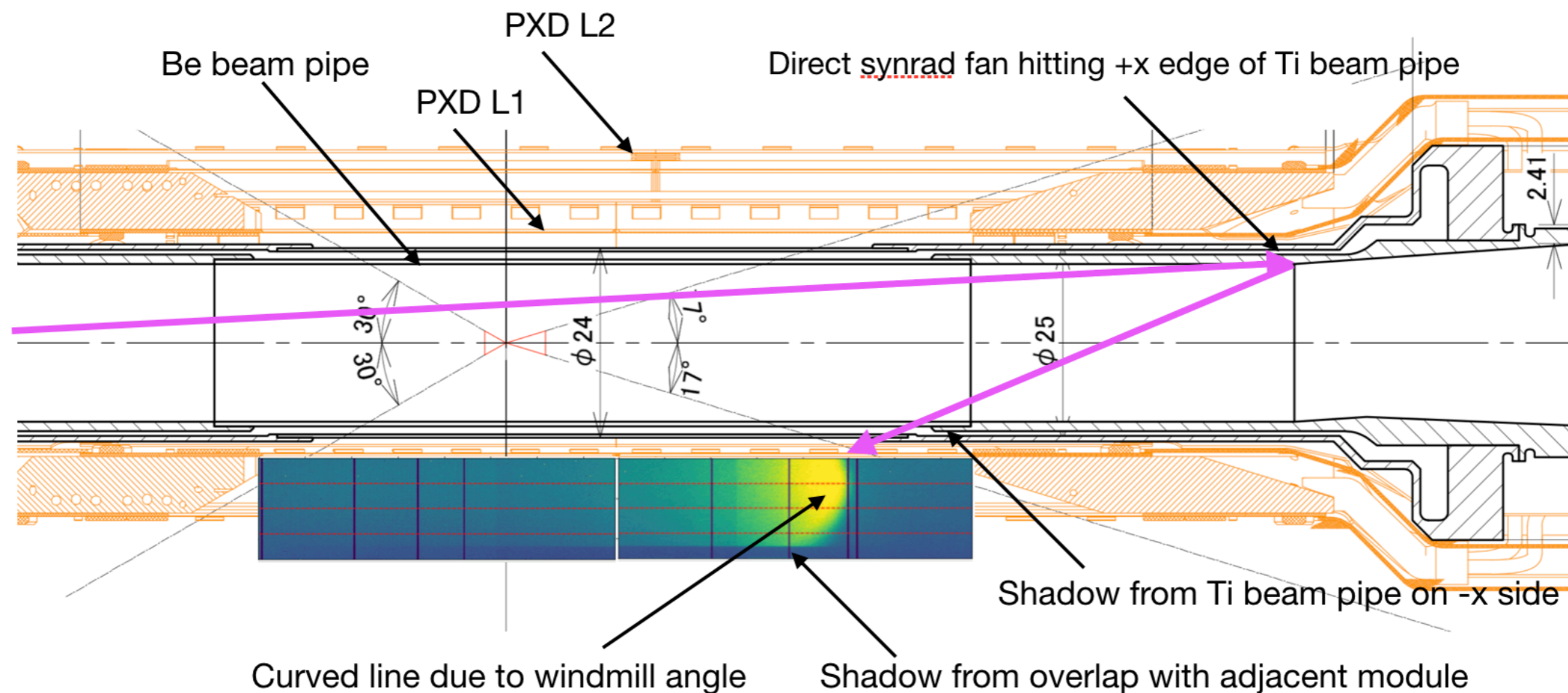


Compensation for Radiation Damage

- ❖ Defects of SiO₂ cause shift of threshold voltage.
- ❖ NIEL is not expected to be an issue.
- ❖ Module still functional after > 25 Mrad (corresponding to 250mrad/s for 10 smy)
- ❖ In Phase3 operation, voltages are regularly adjusted to have the source current of ~100mA.
 - ❖ Tune the internal amplification
 - ❖ Tune the coupling between internal gate and clear.



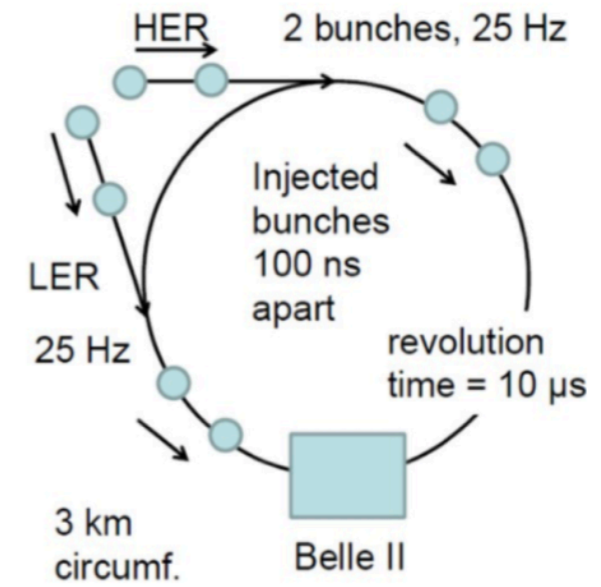
Synchrotron Radiation Background



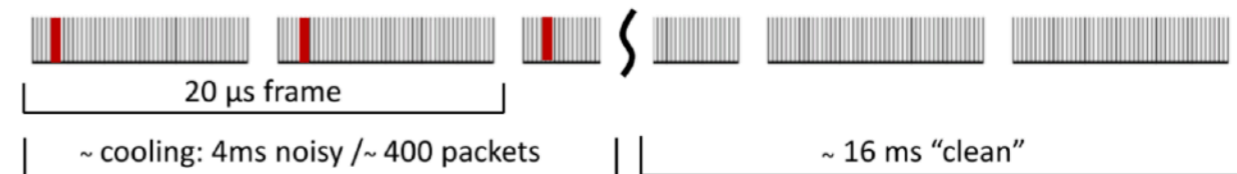
- ❖ IR designed such that no direct SR photons hit the central Be beam pipe.
- ❖ Large SR background was observed for some runs in a few modules in -x direction.
 - ❖ Secondary photons — single pixels, low energy (<10keV)
 - ❖ Back scattering photons from direct synrad fan hitting +x edge of Ti beam pipe
 - ❖ photons which may be originated from synrad that backscatters further downstream
- ❖ May cause inhomogeneous irradiation

Gated Mode Operation

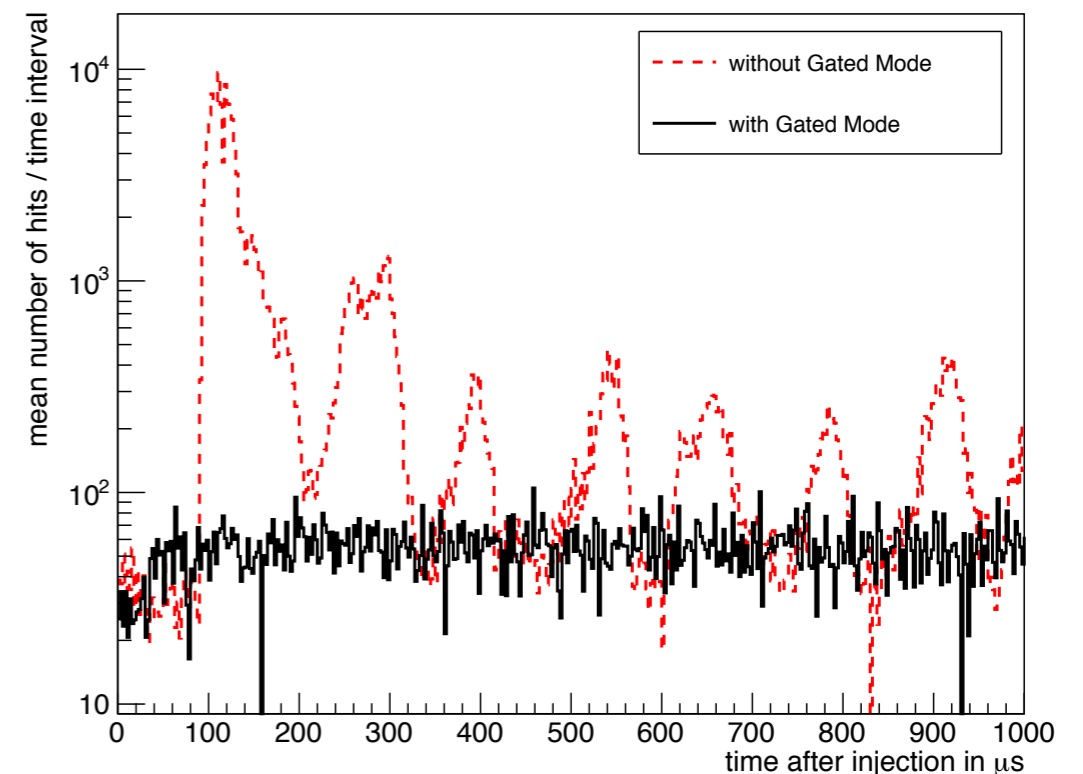
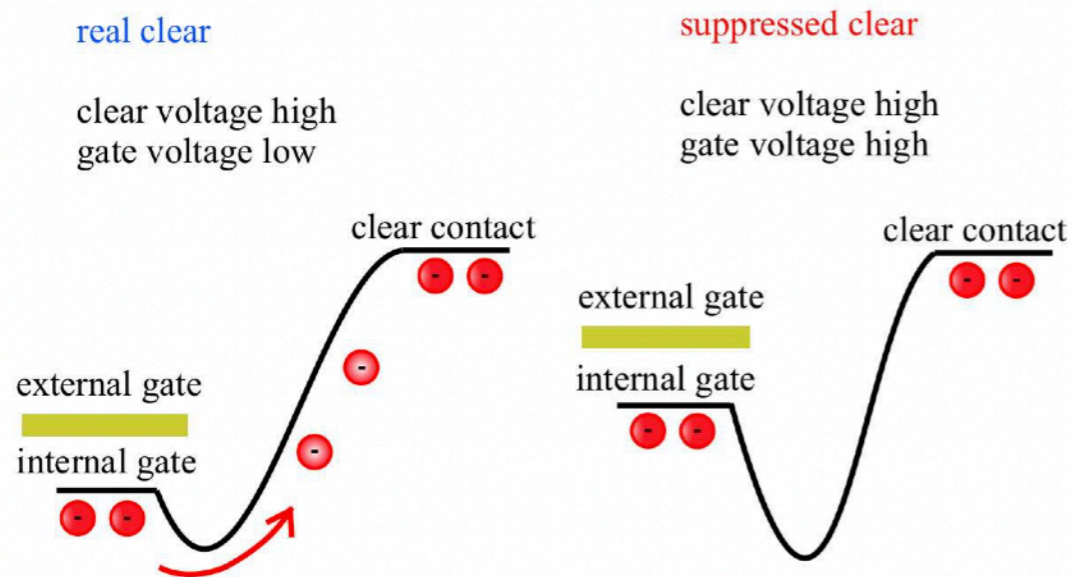
- ❖ SuperKEKB is operated in top-up mode: continuous injection
 - ❖ At design luminosity Touschek effects limit beam life time to 10 mins
 - ❖ Accumulating integrated luminosity effectively.
- ❖ Freshly injected bunches produce high background
 - ❖ Damping time few ms
- ❖ Gated Mode can blind PXD when noisy bunches pass.
 - ❖ Newly created charges are not collected
 - ❖ Charges in internal gate are preserved



SuperKEKB bunch pattern

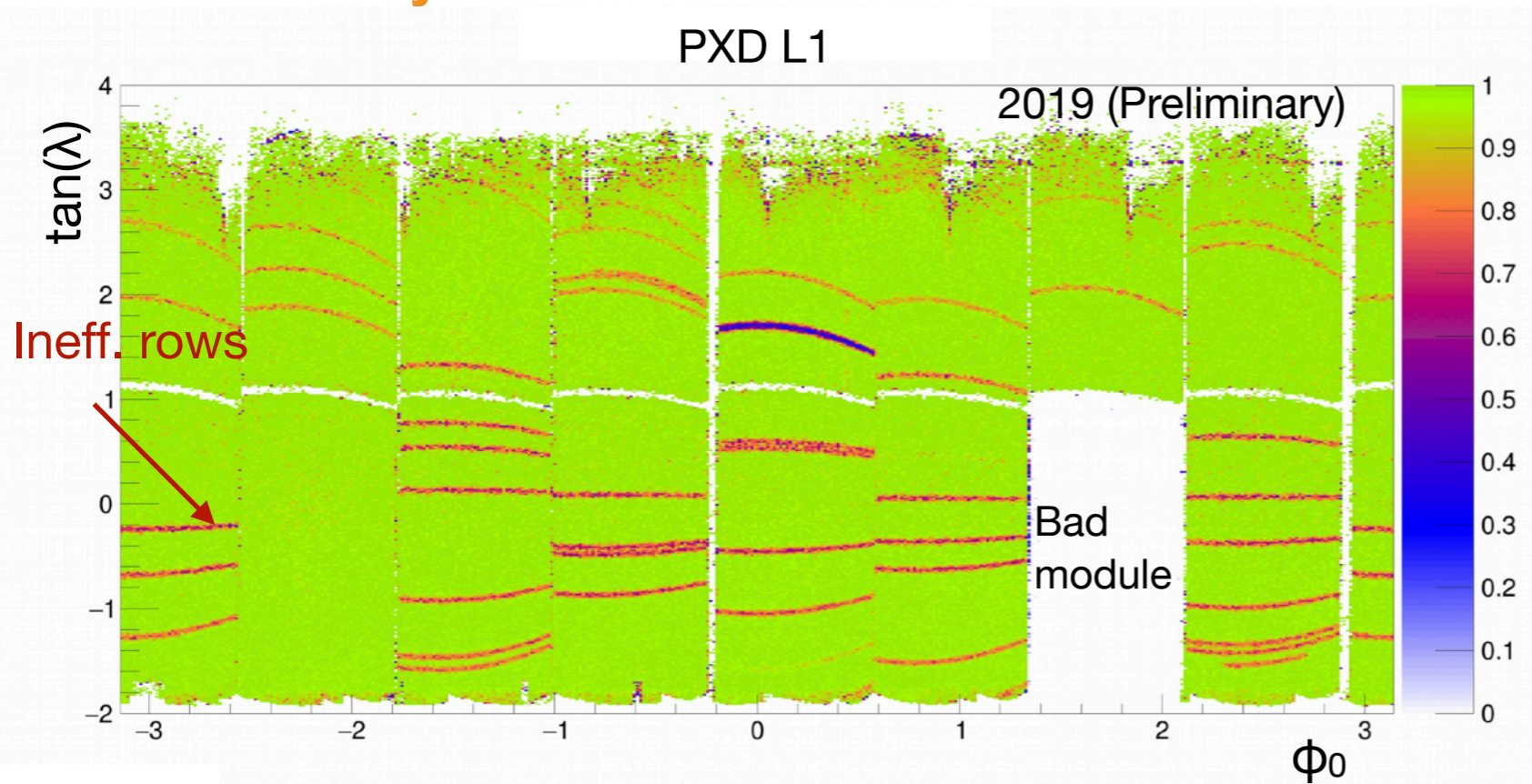


DEPFET Gated Mode



PXD Operation & Performance

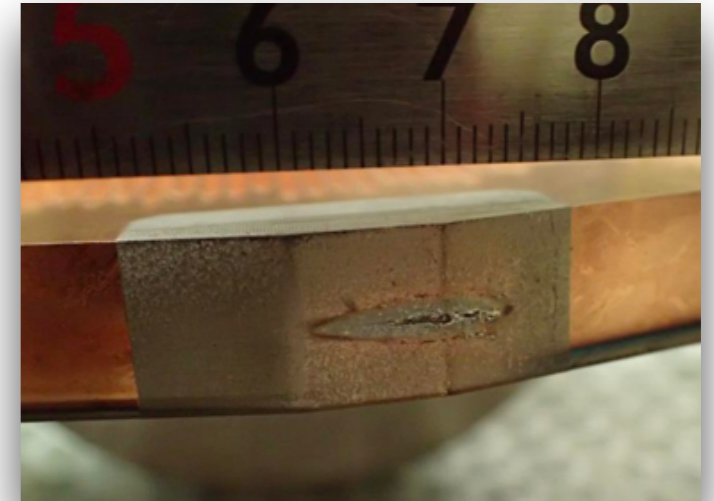
Hit Efficiency



$\lambda \equiv \pi/2 - \theta$, angle between a track and the plane \perp to the beam.

LER beam loss event

- ❖ 150mA beam current lost in 40 μ s, estimated dose in PXD: ~ 5 Gy (0.5krad).
- ❖ Severely damaged vertical collimator
- ❖ Major quench of final focus magnet system
- ❖ Damage in PXD

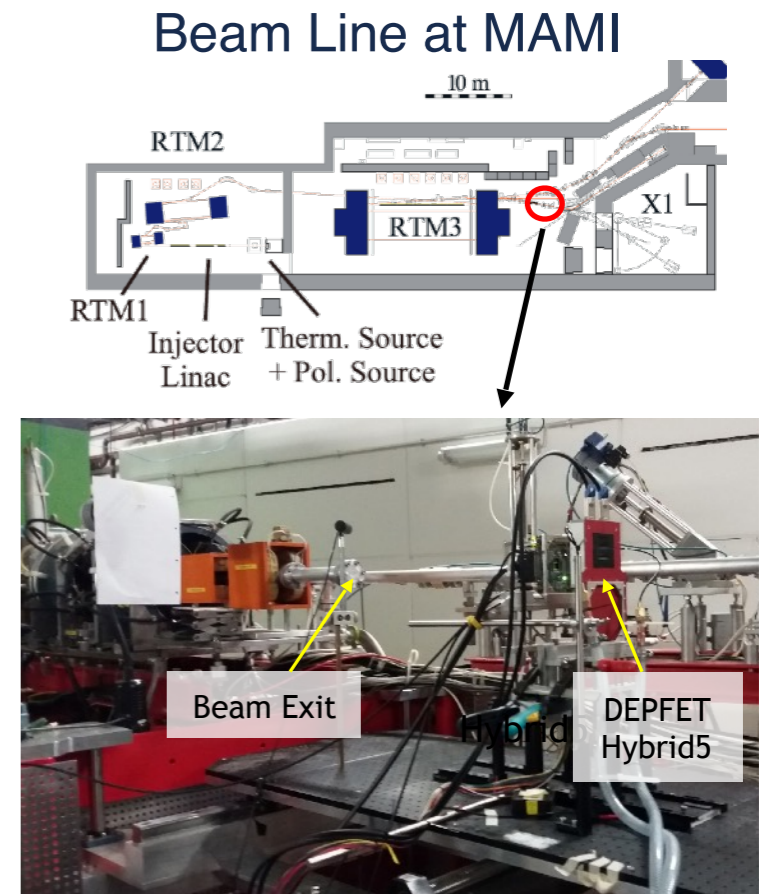
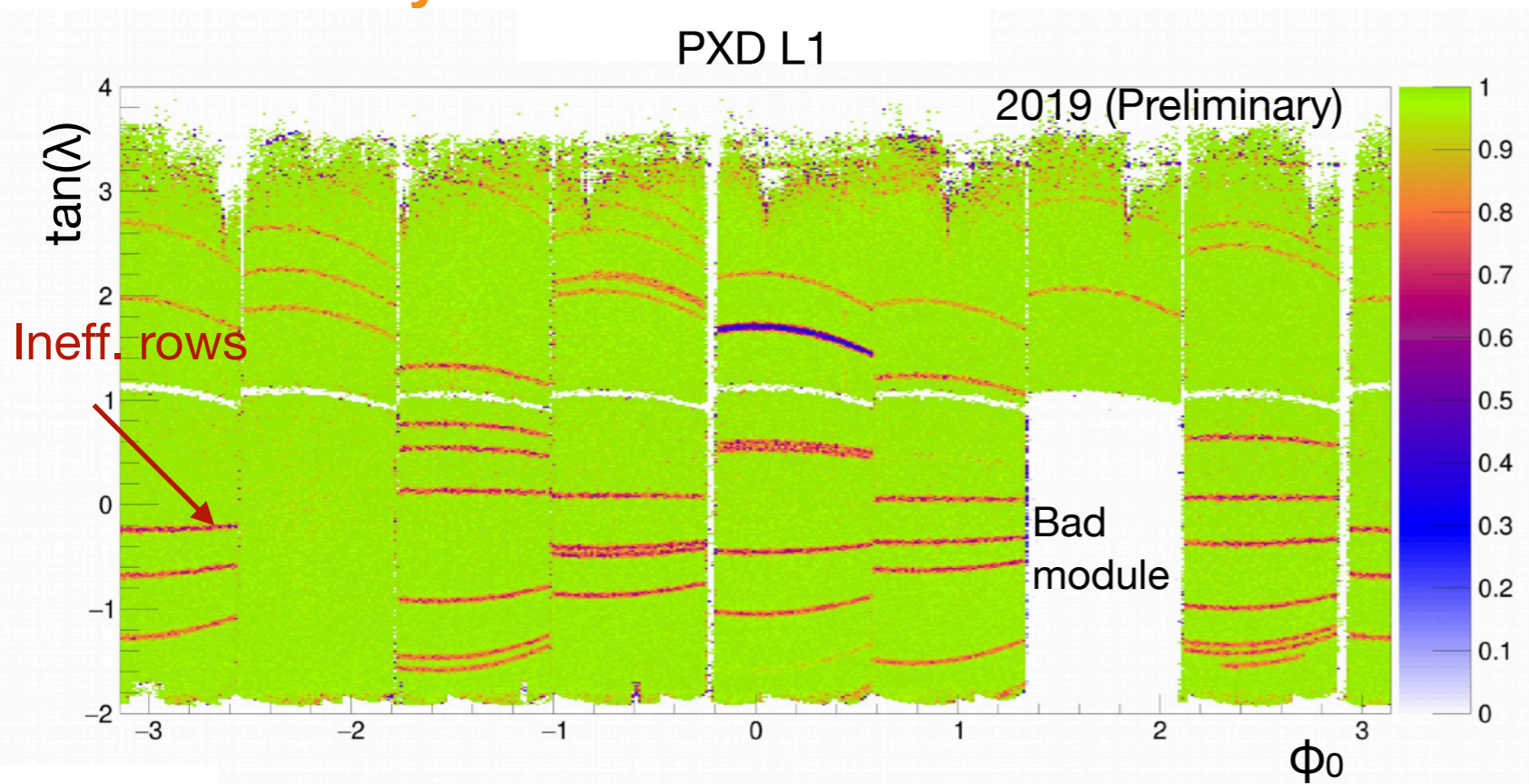


The high radiation dose in the beam loss is a threat to the machine (collimator, final focus magnets) and pixel detector.

- ❖ Inoperable PXD module, recovered afterwards.
- ❖ Working point shifted.
- ❖ Increased number of inefficient rows ($\sim 2\%$). \rightarrow points to possible damages in Switcher

PXD Operation & Performance

Hit Efficiency

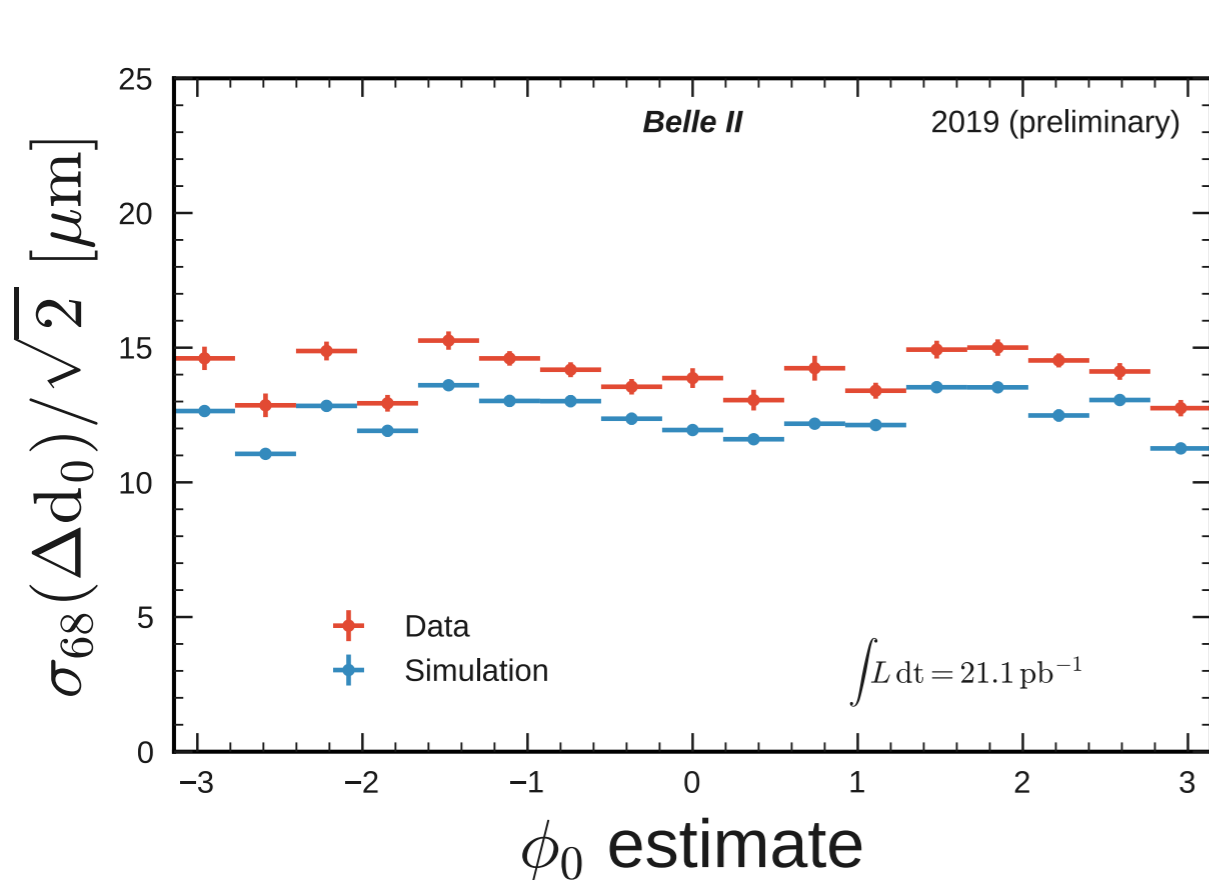
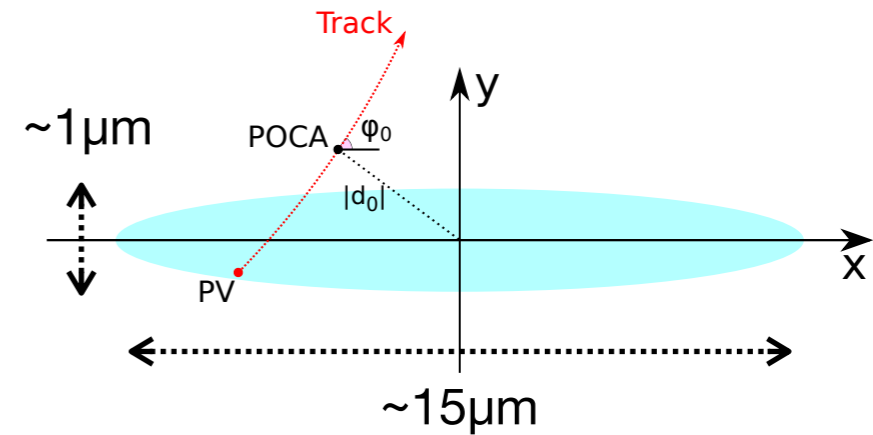


- ❖ Radiation burst tolerance Study
 - ❖ Switchers and DEPFET matrix have been irradiated with a focused pencil beam of electrons (855 MeV) at MAMI, Mainz
 - ❖ A particular region of the Switchers where the voltage regulators is located, is found to be sensitive to the radiation bursts.
 - ❖ The dose is compatible with the estimate at the beam incidents.
- ❖ Improving the protection scheme
 - ❖ PXD: the scheme of fast emergency shutdown is prepared, $O(100\text{ms}) \rightarrow O(100\mu\text{s})$
 - ❖ Machine side: faster abort logic , increase number of abort gaps (1- \rightarrow 2), modify the collimator system.

VXD Performance

Transverse Impact Parameter Resolution

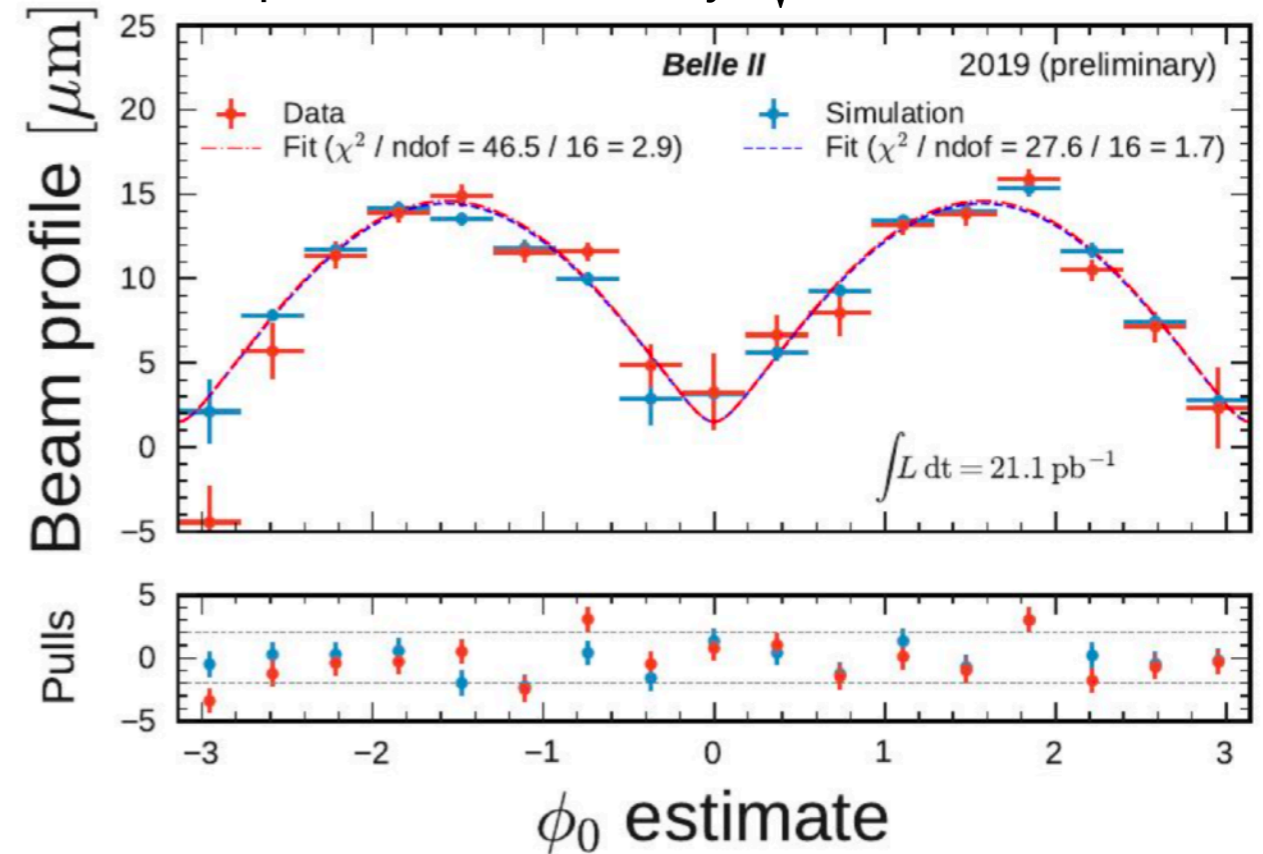
- ❖ Exploit small and flat transverse beam spot size in SuperKEKB
 - ❖ Use ϕ -dependence of track impact parameter (d_0) resolution to study beam profile
 - ❖ Use dimuon events to measure intrinsic d_0 resolution
- ❖ Unfold the beam profile: size consistent with expectations.



Data: $\sigma_i = 14.1 \pm 0.1 \mu m$

MC: $\sigma_i = 12.5 \pm 0.1 \mu m$

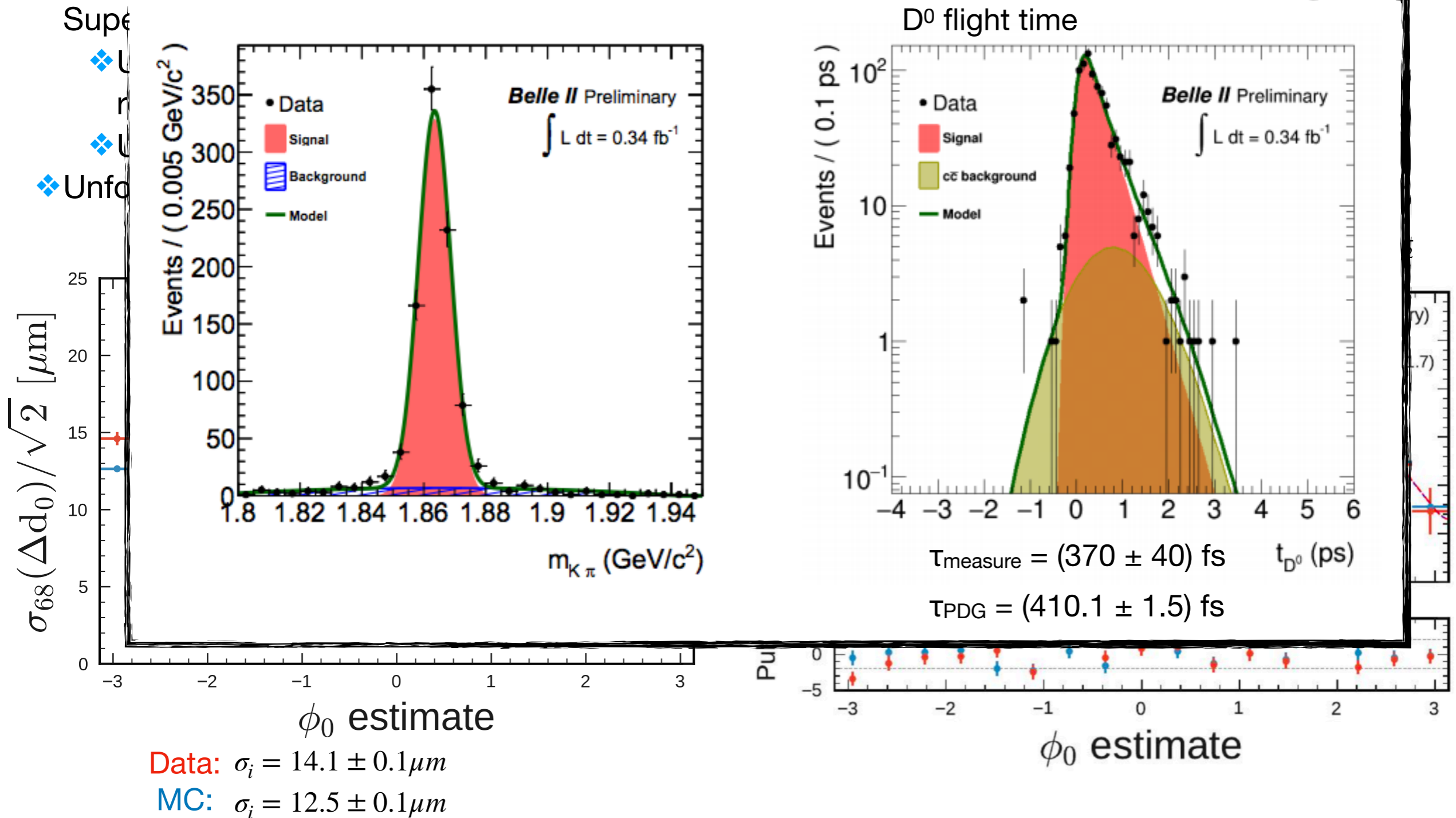
Beam profile described by $\sqrt{(\tilde{\sigma}_x \sin \phi_0)^2 + (\tilde{\sigma}_y \cos \phi_0)^2}$



VXD Performance

Transverse Impact Parameter Resolution

- Exploit small and flat transverse beam spot size in



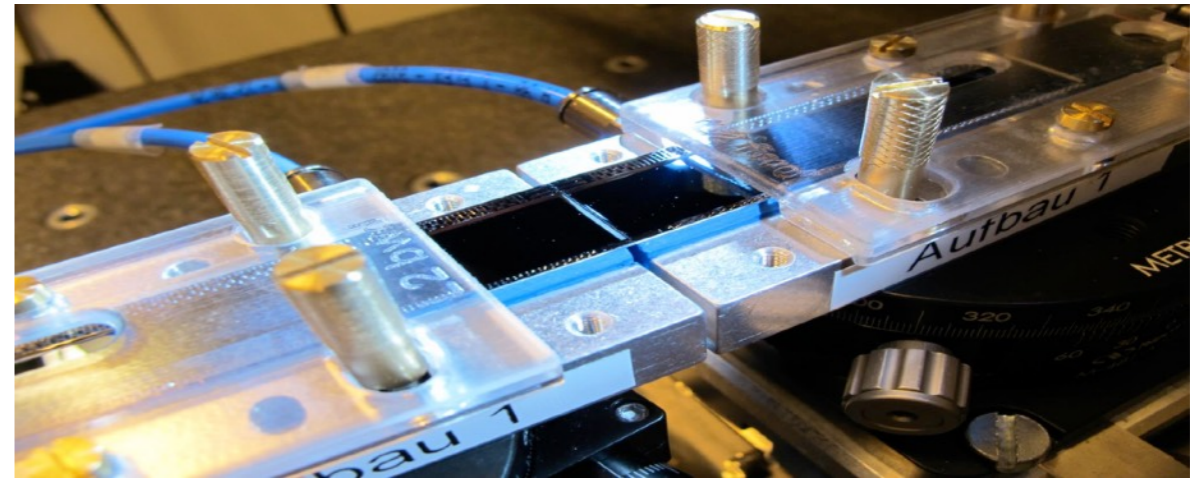
Summary

- ❖ The first beam collision experience with the new pixel concept (DEPFET) and half of the full scaled detector has been achieved.
 - ❖ Challenging operating conditions close to the IP at a very ambitious machine like SuperKEKB
- ❖ PXD system has been continuously improved and optimized during the 2019 runs.
- ❖ Good PXD performance is demonstrated.
- ❖ Irradiation damage to PXD from beam loss events is under investigation.
 - ❖ SuperKEKB and Belle II need to minimize the probability and impact of major uncontrolled beam losses.
 - ❖ Protection scheme is being improved.

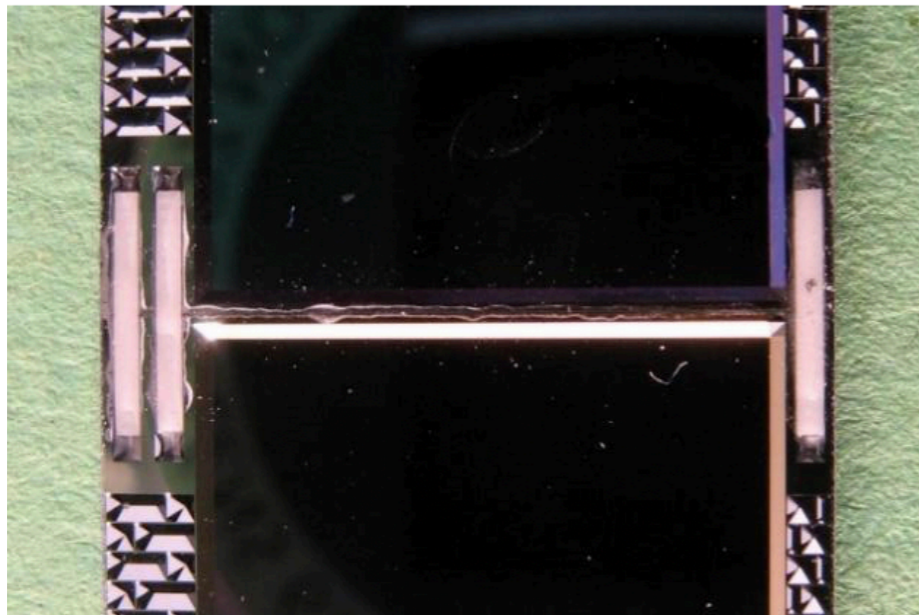
Backup

Ladder Gluing

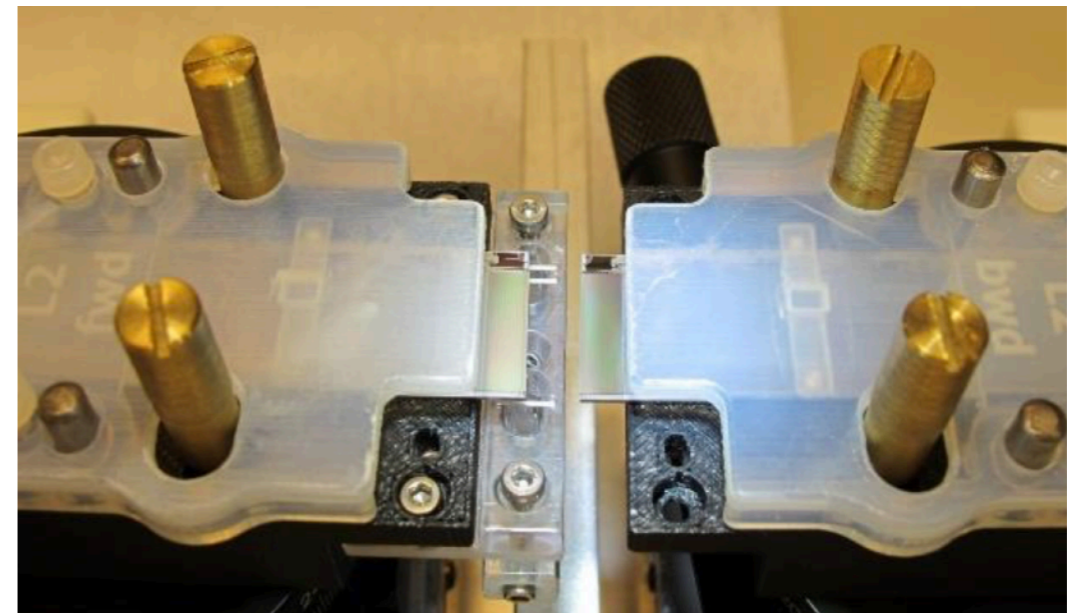
- ❖ De-scoped PXD was installed in 2018/2019,
 - ❖ Due to relatively high failure rate in ladder gluing procedure → solved!
 - ❖ Replacement with full PXD is scheduled in 2021.



Improved ladder gluing scheme

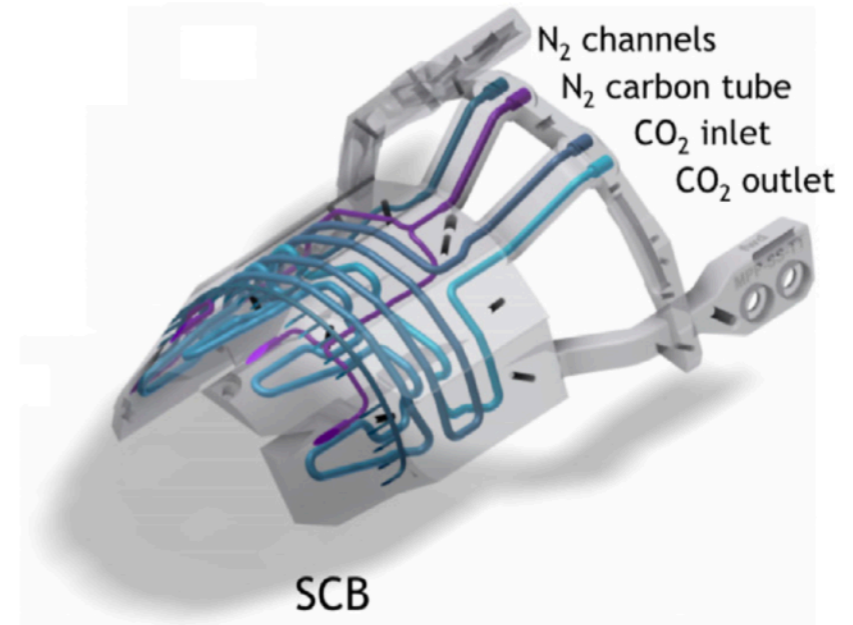


Small ceramic inserts on the back side
→ reinforcement of the joint



Thermal Management

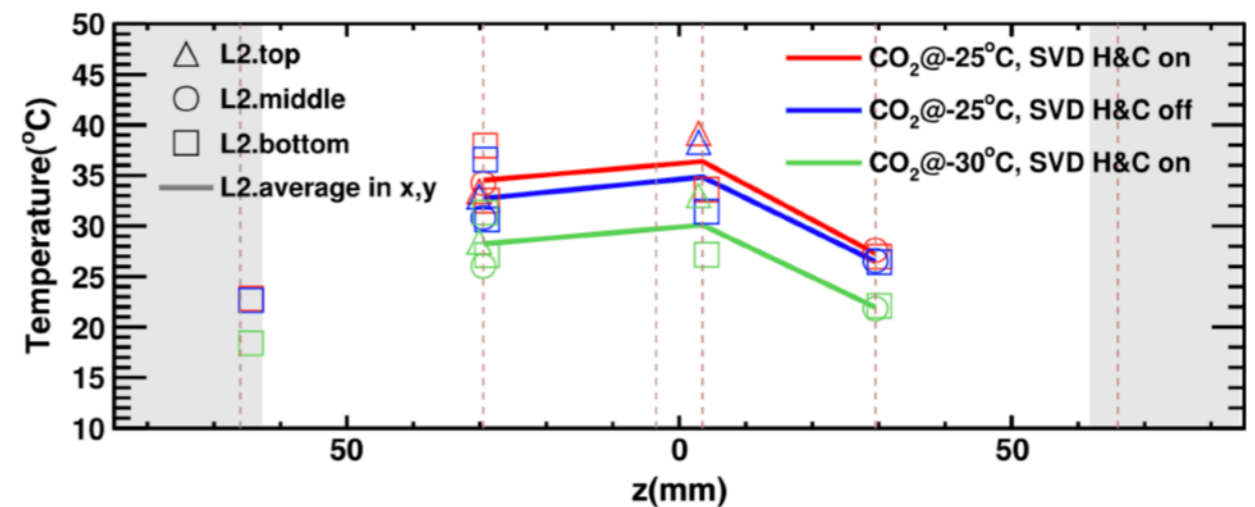
- ❖ The power consumption of full PXD is 420W,
 - ❖ 360W are contributed from DCD/DHP, which are located in the end of stave.
 - ➔ Active 2 phase CO₂ cooling is required there.
 - ❖ Little power derived from matrix (0.5W per module) and Switchers (1W per module)
 - ➔ Forced N₂ cooling is sufficient in the sensitive area.



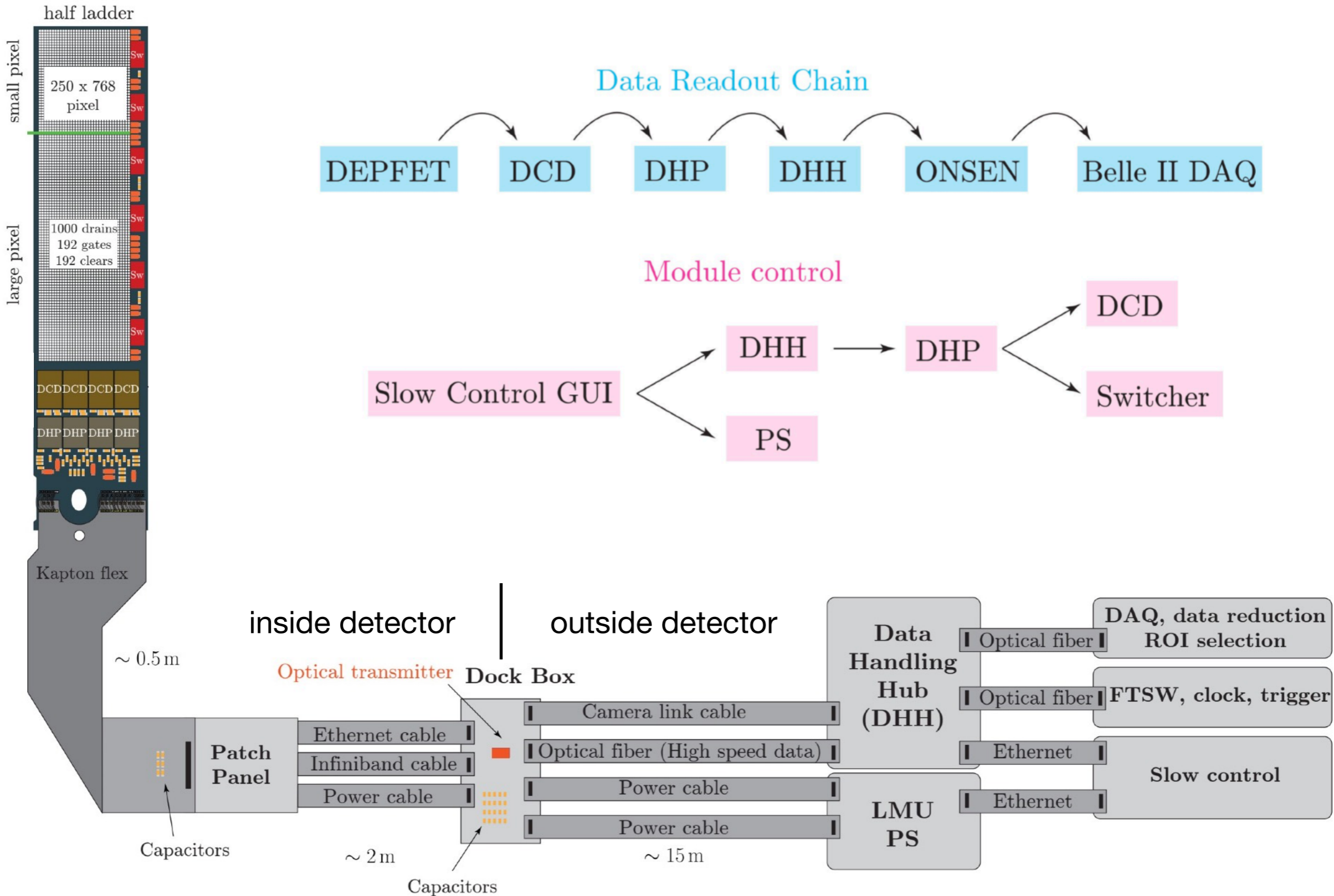
Thermal mock-up (half-shell)



Temperature along the PXD ladder



PXD Layout



Module Calibration

- ❖ Optimization of ASIC and DEPFET parameters, e.g.
 - ❖ DHP input delay elements
 - ❖ DCD internal current source
 - ❖ charge collection
- ❖ Narrow and stable pedestals
- ❖ Low noise ($<1\text{ADU}$, $<100e$ ENC)

ADC Transfer Curve

